

V_{DSS}	600V
$R_{DS(on)}$ (Max.)	0.102Ω
I_D	35A
P_D	120W

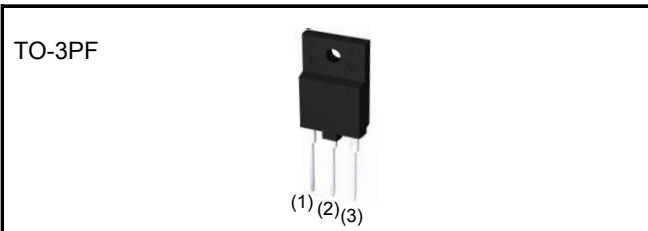
●Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be $\pm 20V$.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating ; RoHS compliant

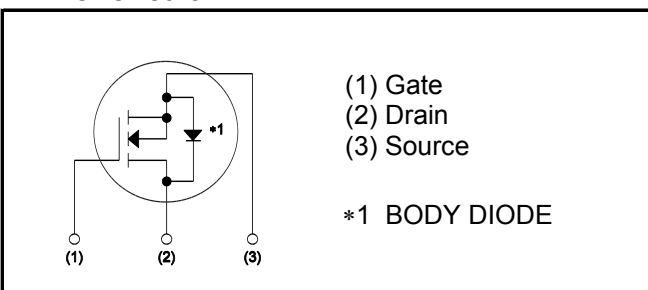
●Application

Switching Power Supply

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Tube
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	360
	Taping code	C8
	Marking	R6035ENZ

●Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	600	V
Continuous drain current	$T_c = 25^\circ C$	I_D^{*1}	± 35	A
	$T_c = 100^\circ C$	I_D^{*1}	± 19	A
Pulsed drain current		$I_{D,pulse}^{*2}$	± 105	A
Gate - Source voltage		V_{GSS}	± 20	V
Avalanche energy, single pulse		E_{AS}^{*3}	796	mJ
Avalanche energy, repetitive		E_{AR}^{*3}	1.2	mJ
Avalanche current, repetitive		I_{AR}	6.6	A
Power dissipation ($T_c = 25^\circ C$)		P_D	120	W
Junction temperature		T_j	150	$^\circ C$
Range of storage temperature		T_{stg}	-55 to +150	$^\circ C$
Reverse diode dv/dt		dv/dt *4	15	V/ns

●Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 480V$ $T_j = 125^\circ C$	50	V/ns

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R_{thJC}	-	-	1.04	$^\circ C/W$
Thermal resistance, junction - ambient	R_{thJA}	-	-	40	$^\circ C/W$
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	$^\circ C$

●Electrical characteristics ($T_a = 25^\circ C$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	600	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 600V, V_{GS} = 0V$ $T_j = 25^\circ C$	-	0.1	100	μA
		$T_j = 125^\circ C$	-	-	1000	
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = 10V, I_D = 1mA$	2	-	4	V
Static drain - source on - state resistance	$R_{DS(on)}^{*5}$	$V_{GS} = 10V, I_D = 18.1A$ $T_j = 25^\circ C$	-	0.092	0.102	Ω
		$T_j = 125^\circ C$	-	0.200	-	
Gate input resistance	R_G	$f = 1MHz, \text{open drain}$	-	1.5	-	Ω

●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Transconductance	g_{fs}^{*5}	$V_{DS} = 10\text{V}$, $I_D = 17.5\text{A}$	11	22	-	S
Input capacitance	C_{iss}	$V_{GS} = 0\text{V}$	-	2720	-	pF
Output capacitance	C_{oss}	$V_{DS} = 25\text{V}$	-	2000	-	
Reverse transfer capacitance	C_{rss}	$f = 1\text{MHz}$	-	240	-	
Effective output capacitance, energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$ $V_{DS} = 0\text{V to } 480\text{V}$	-	100	-	pF
Effective output capacitance, time related	$C_{o(tr)}$		-	500	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \approx 300\text{V}$, $V_{GS} = 10\text{V}$	-	40	-	ns
Rise time	t_r^{*5}	$I_D = 17.5\text{A}$	-	80	-	
Turn - off delay time	$t_{d(off)}^{*5}$	$R_L = 17.4\Omega$	-	210	-	
Fall time	t_f^{*5}	$R_G = 10\Omega$	-	80	-	

●Gate Charge characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g^{*5}	$V_{DD} \approx 300\text{V}$	-	110	-	nC
Gate - Source charge	Q_{gs}^{*5}	$I_D = 35\text{A}$	-	15	-	
Gate - Drain charge	Q_{gd}^{*5}	$V_{GS} = 10\text{V}$	-	60	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} \approx 300\text{V}$, $I_D = 35\text{A}$	-	6.0	-	V

*1 Limited only by maximum temperature allowed.

*2 $P_W \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 $I_D = 6.6\text{A}$, $V_{DD} = 50\text{V}$

*4 Reference measurement circuits Fig.5-1.

*5 Pulsed

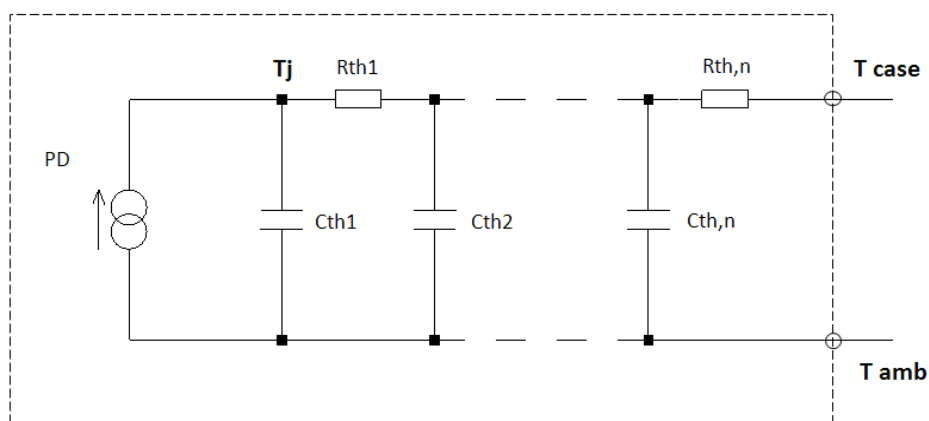
●Body diode electrical characteristics (Source-Drain) ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_S^{*1}	$T_c = 25^\circ\text{C}$	-	-	35	A
Inverse diode direct current, pulsed	I_{SM}^{*2}		-	-	105	A
Forward voltage	V_{SD}^{*5}	$V_{GS} = 0\text{V}, I_S = 10\text{A}$	-	-	1.5	V
Reverse recovery time	t_{rr}^{*5}	$I_S = 35\text{A}$ $di/dt = 100\text{A}/\mu\text{s}$	-	780	-	ns
Reverse recovery charge	Q_{rr}^{*5}		-	16.5	-	μC
Peak reverse recovery current	I_{rrm}^{*5}		-	45	-	A

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R_{th1}	0.0683	K/W
R_{th2}	0.402	
R_{th3}	1.22	

Symbol	Value	Unit
C_{th1}	0.00697	Ws/K
C_{th2}	0.0677	
C_{th3}	1.12	



●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

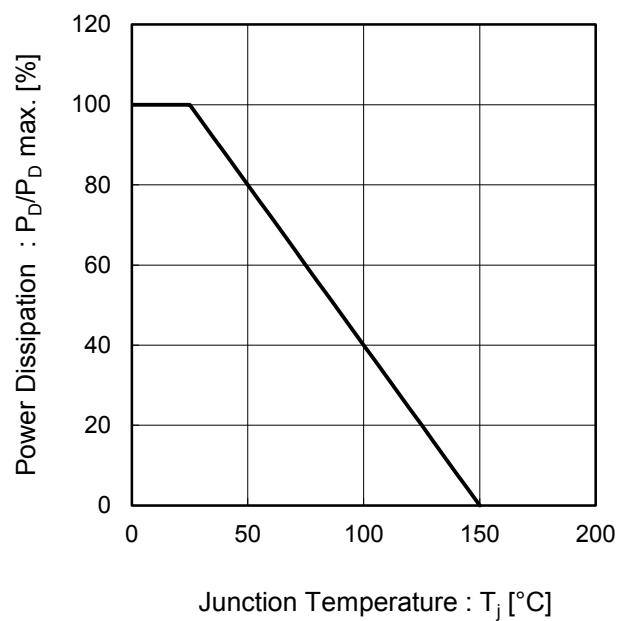


Fig.2 Normalized Transient Thermal Resistance vs. Pulse Width

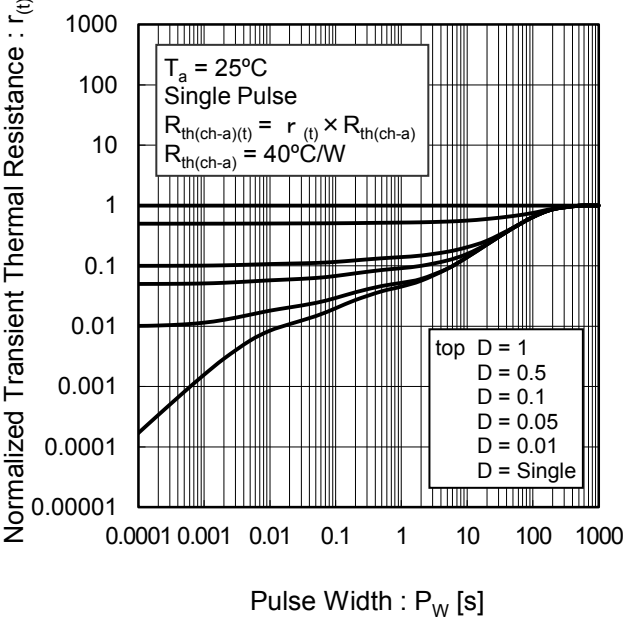
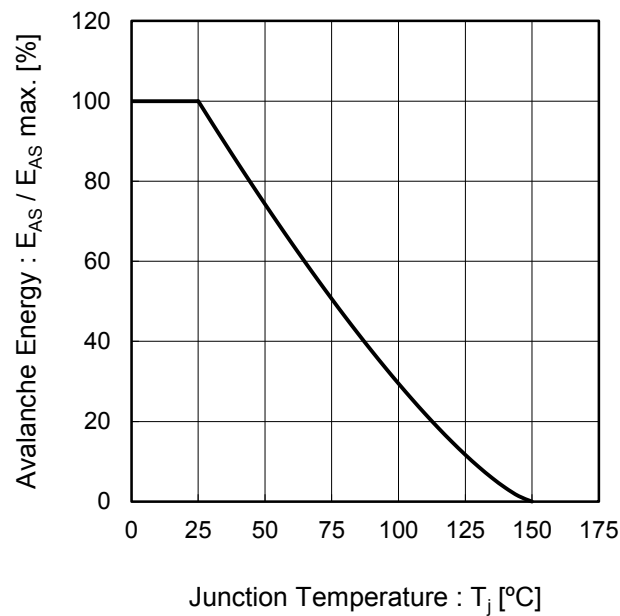


Fig.3 Avalanche Energy Derating Curve vs Junction Temperature



●Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)

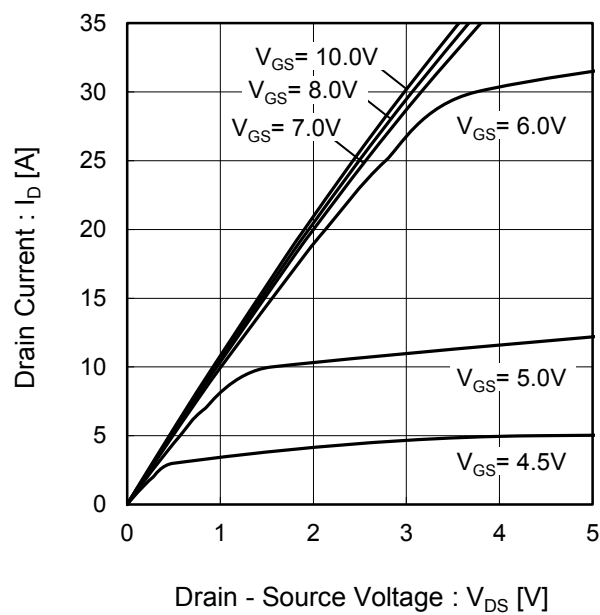


Fig.5 Typical Output Characteristics(II)

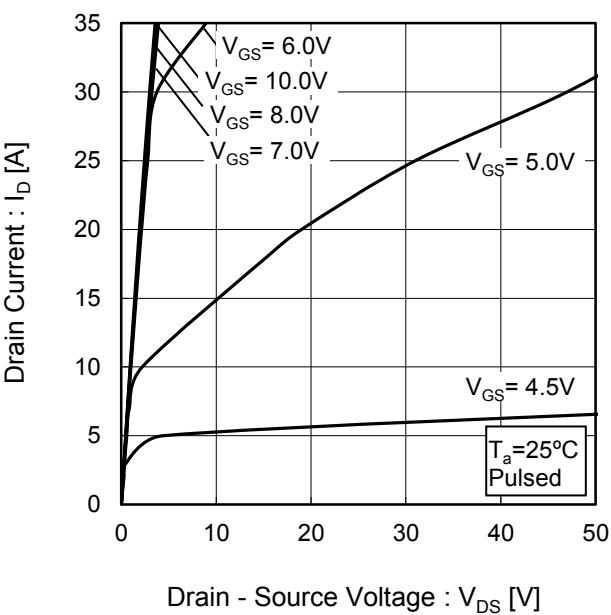


Fig.6 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(I)

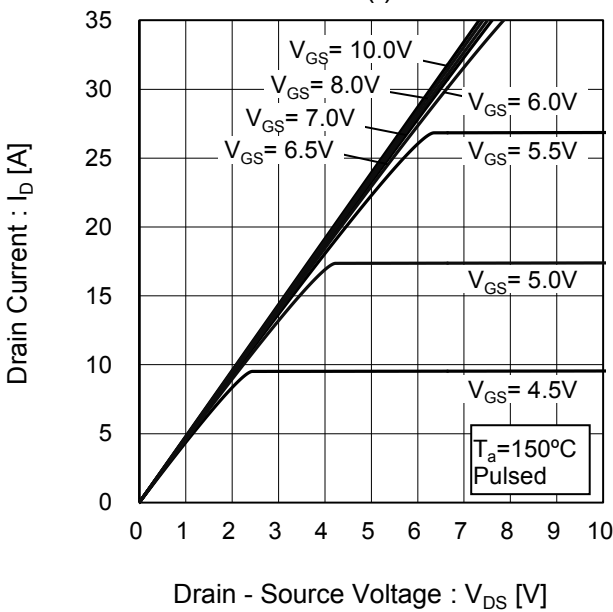
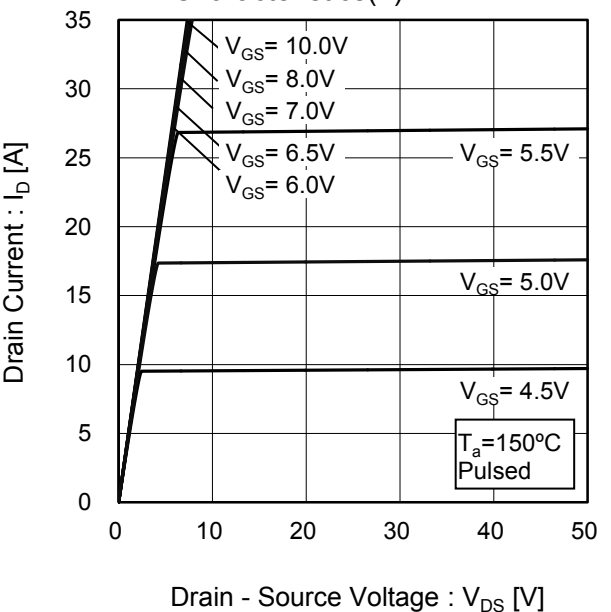
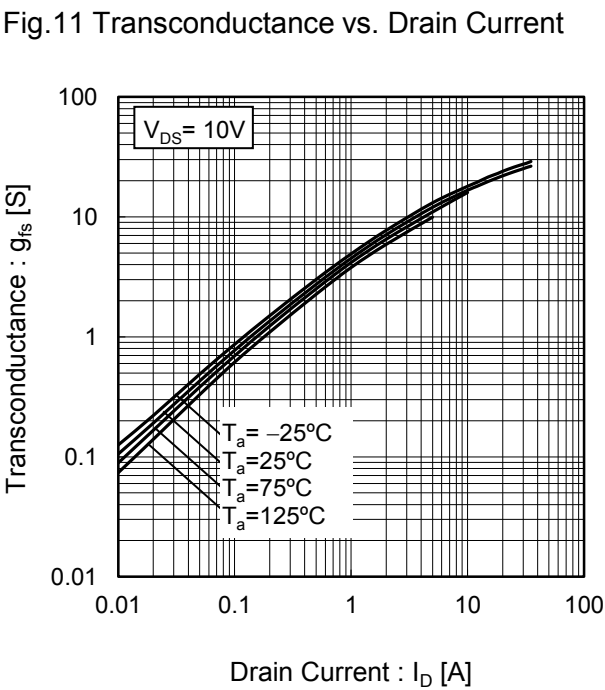
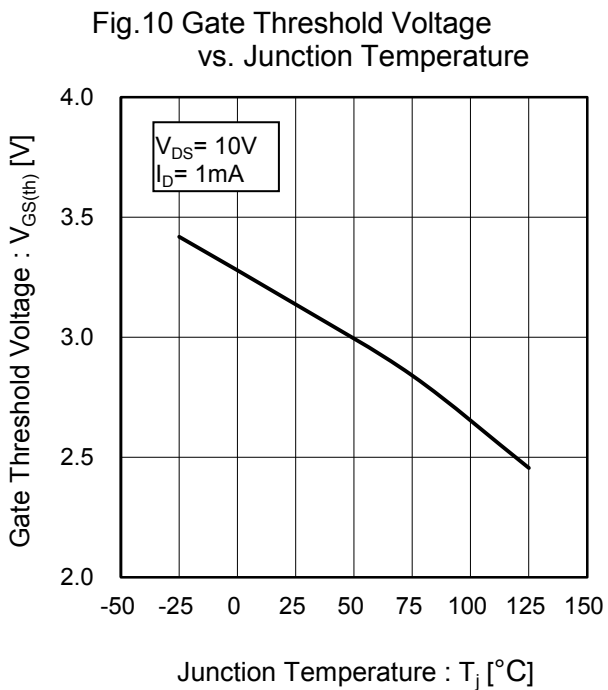
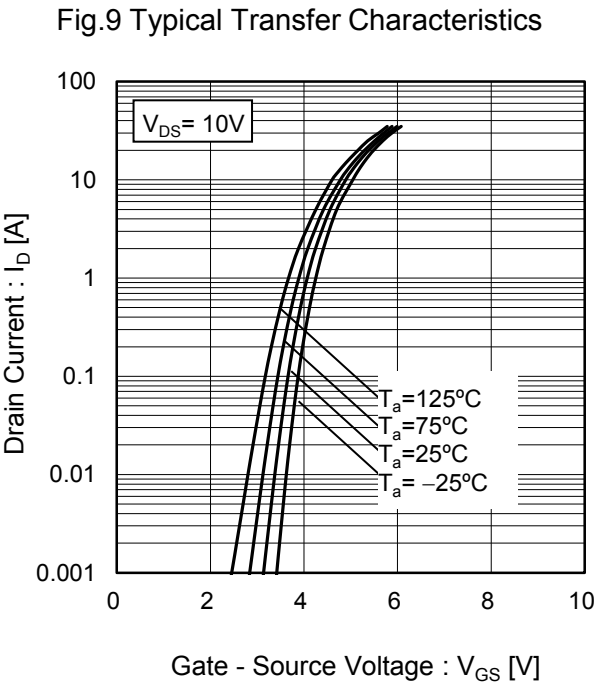
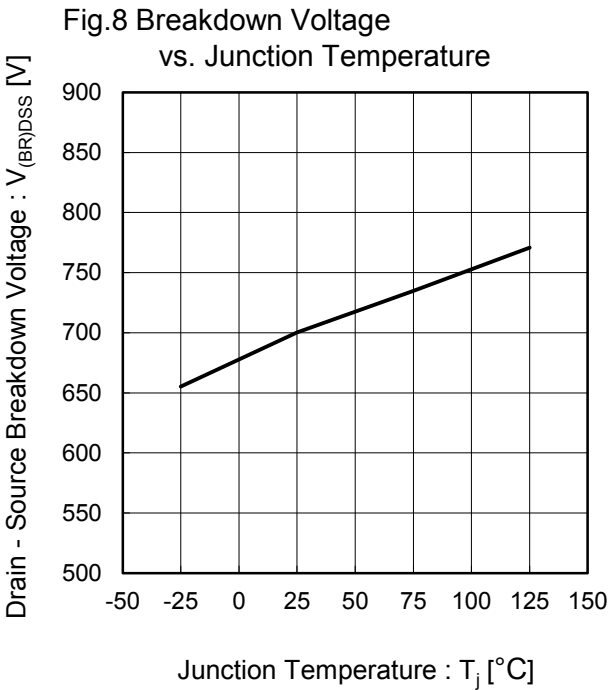


Fig.7 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(II)



●Electrical characteristic curves



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

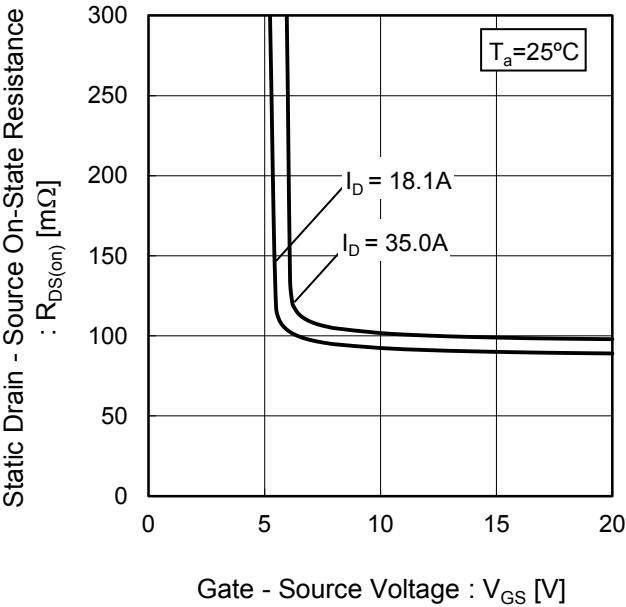


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

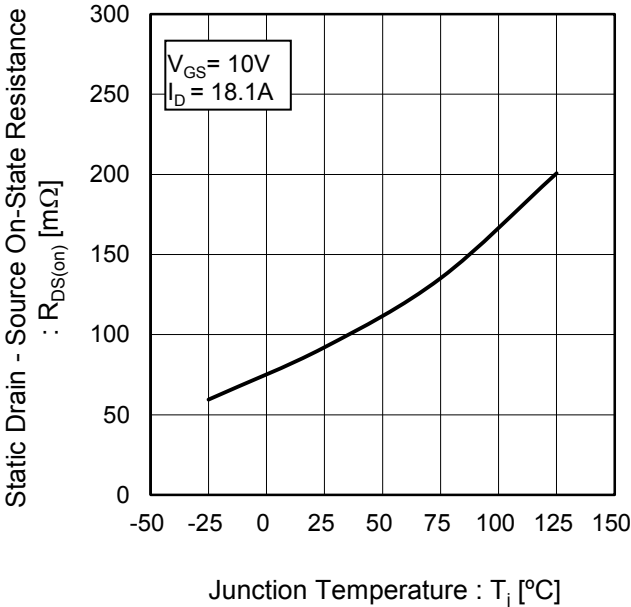


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current

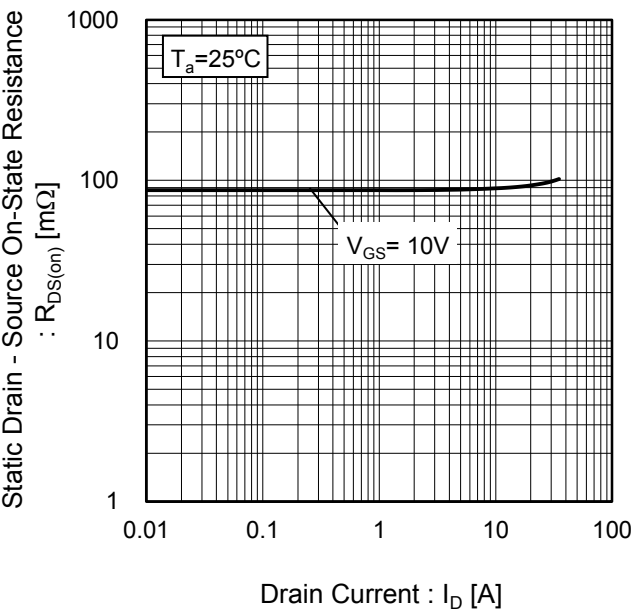
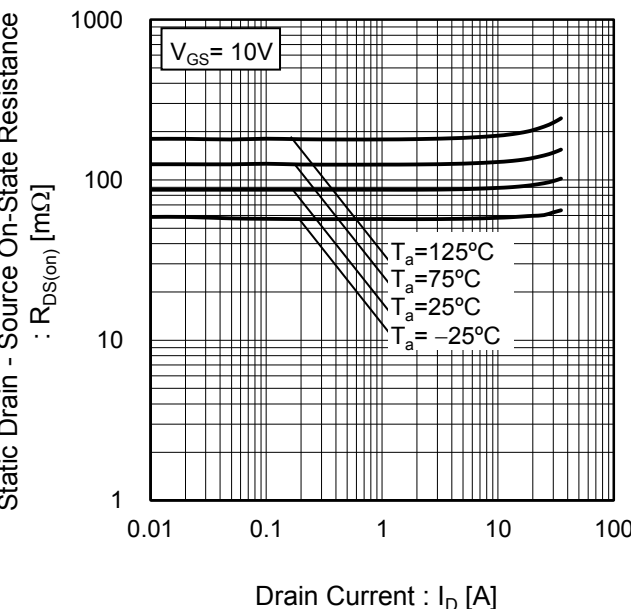


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current



●Electrical characteristic curves

Fig.16 Typical Capacitance vs. Drain - Source Voltage

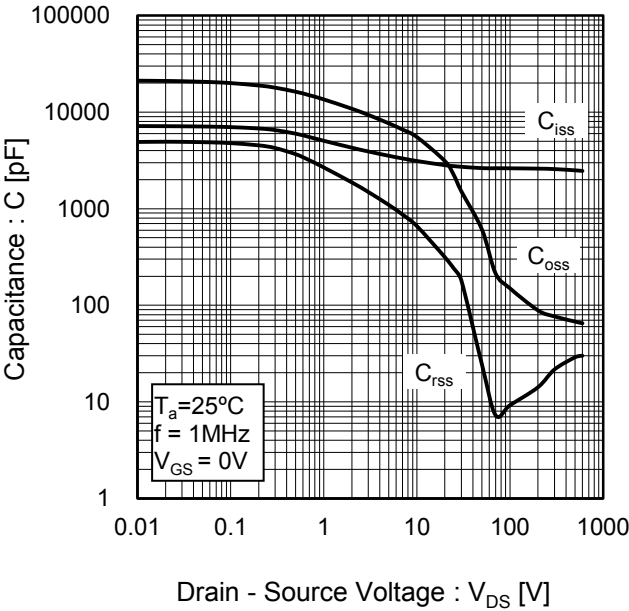


Fig.17 Coss Stored Energy

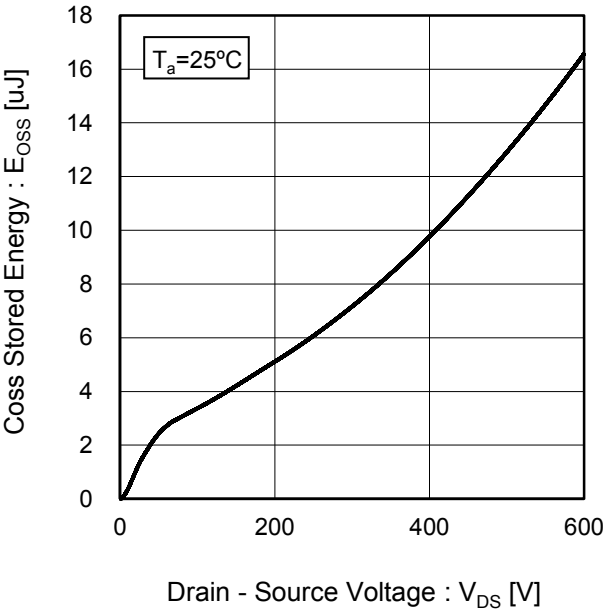


Fig.18 Switching Characteristics

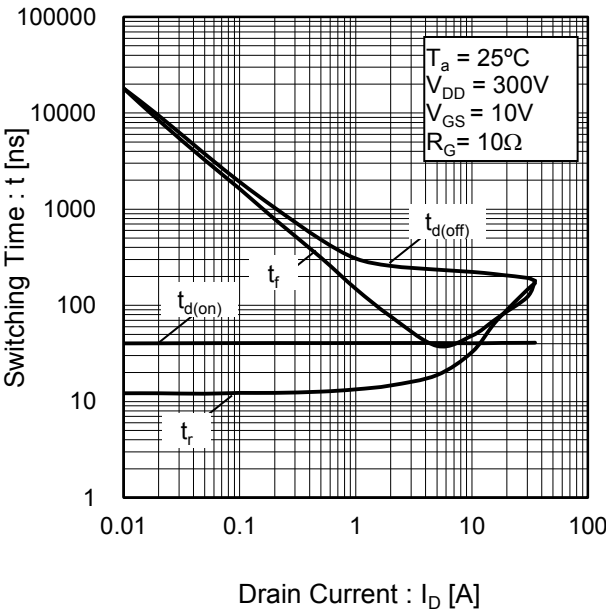
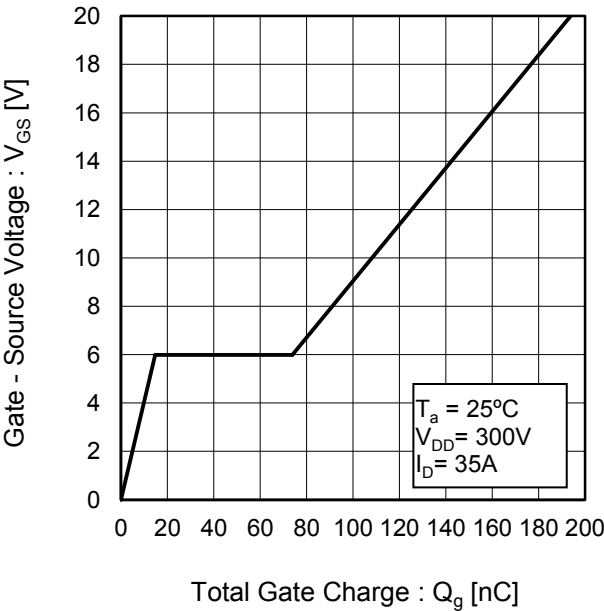


Fig.19 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.20 Inverse Diode Forward Current vs. Source - Drain Voltage

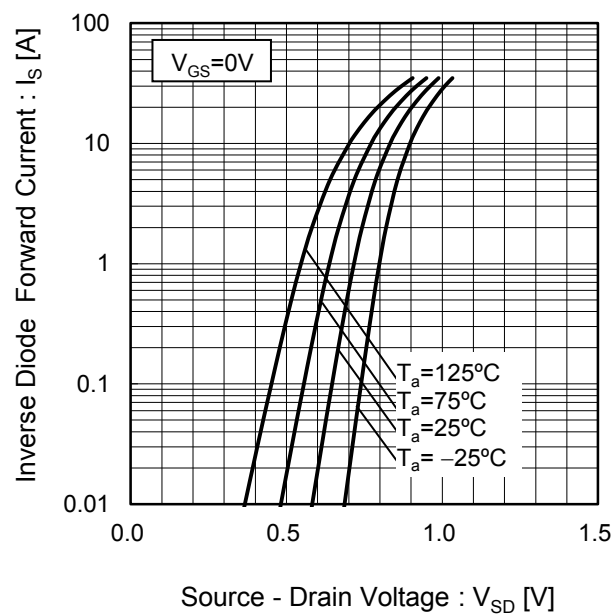
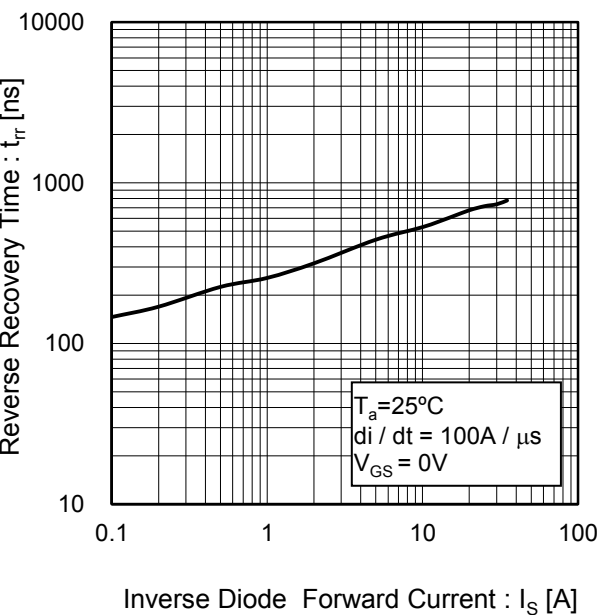


Fig.21 Reverse Recovery Time vs. Inverse Diode Forward Current



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

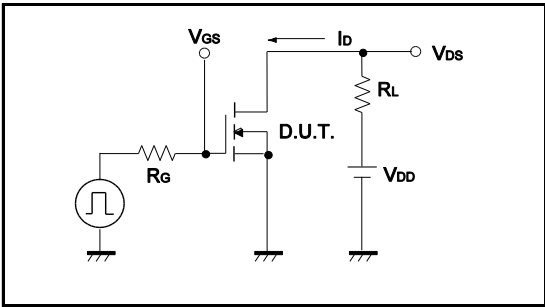


Fig.1-2 Switching Waveforms

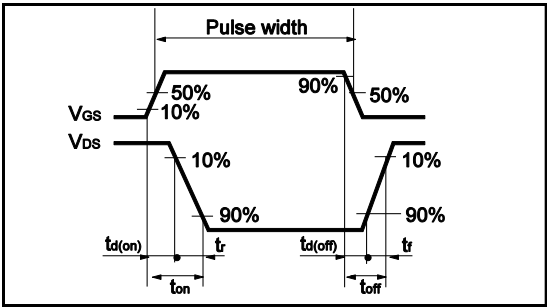


Fig.2-1 Gate Charge Measurement Circuit

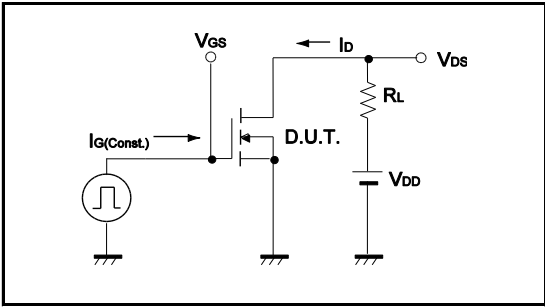


Fig.2-2 Gate Charge Waveform

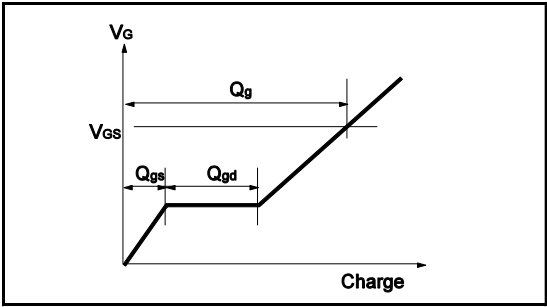


Fig.3-1 Avalanche Measurement Circuit

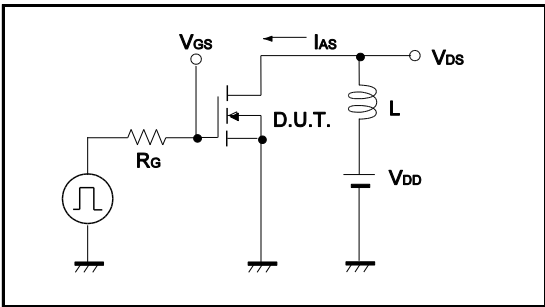


Fig.3-2 Avalanche Waveform

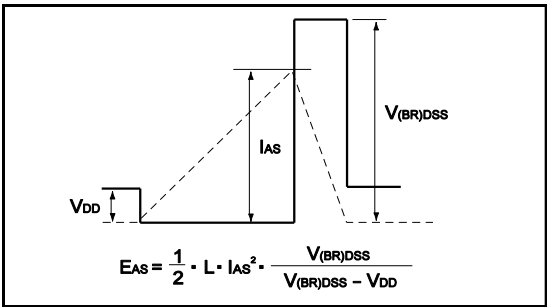


Fig.4-1 dv/dt Measurement Circuit

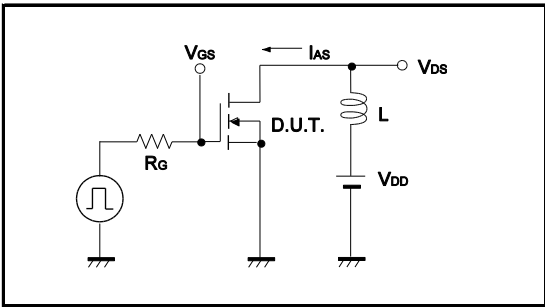


Fig.4-2 dv/dt Waveform

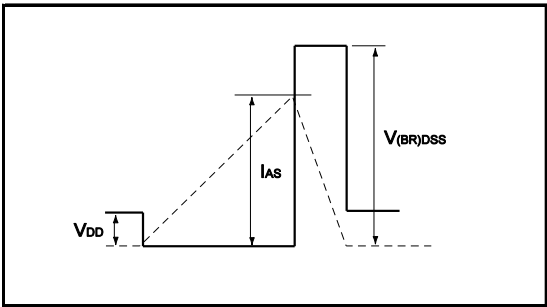


Fig.5-1 di/dt Measurement Circuit

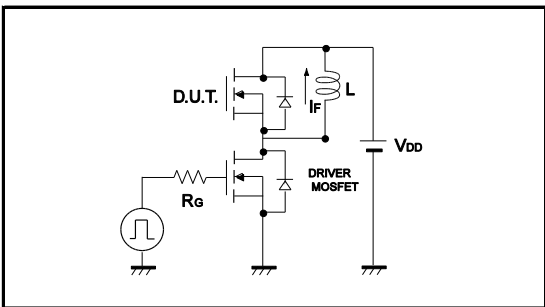
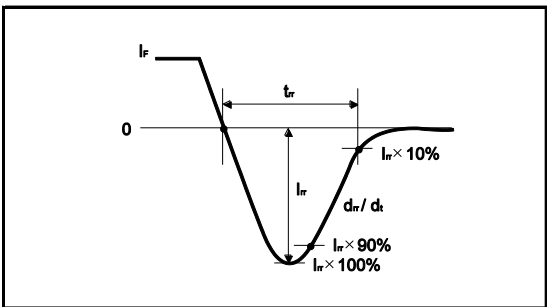
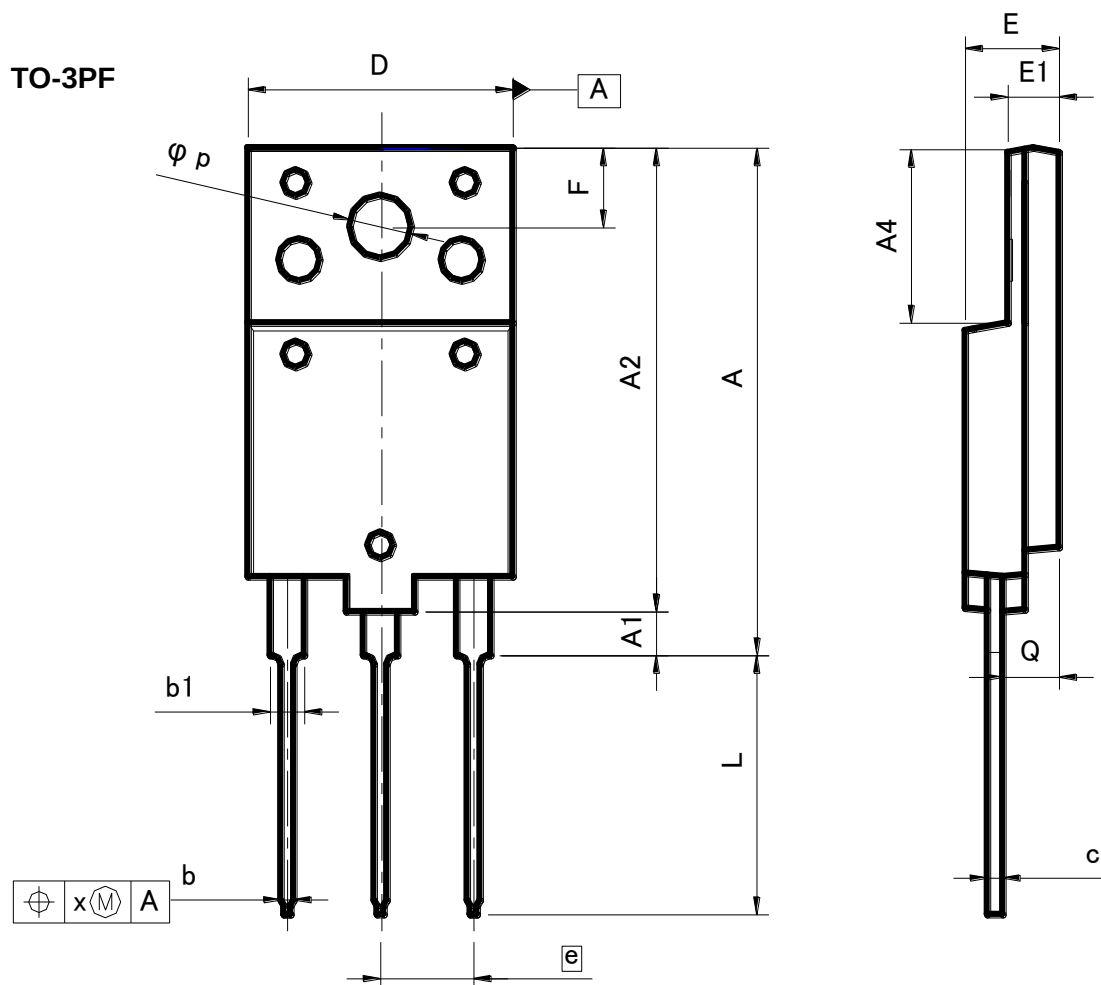


Fig.5-2 di/dt Waveform



●Dimensions (Unit : mm)



DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	26.30	26.70	1.035	1.051
A1	2.30	2.70	0.091	0.106
A2	26.30	26.70	1.035	1.051
A4	9.80	10.20	0.386	0.402
b	0.65	0.95	0.026	0.037
b1	1.80	2.20	0.071	0.087
c	0.80	1.10	0.031	0.043
D	15.30	15.70	0.602	0.618
E	5.30	5.70	0.209	0.224
e	5.45		0.215	-
E1	2.80	3.20	0.110	0.126
F	4.30	4.70	0.169	0.185
L	14.60	15.00	0.575	0.591
p	3.40	3.80	0.134	0.150
Q	3.10	3.50	0.122	0.138
x	-	0.50	-	0.020

Dimension in mm / inches

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